

Drafts

→ BRS:

BRS:

→ BRS:

➔ BRS: knall

➡ BRS: 19:21:23

➡ BRS: 32with 33

Ⓢ Pending

 **Active**

• L2: (27451) contactless contact adj less

• L3: (1866622) vertical

✎ L4: (1986352) channel tft transistor

• L5: (13710) L3 adj L4

2022 2nd year

Failed

 Saved

9 SI: (1) 09/948877

S2: (1736) "KONINKLIJKE PHILIPS".as

➤ S3: (14) Single adj electron adj resistor adj memory

➡ S4: (1403331)channel

✎ S5: (13) (Single adj electron adj resistor adj memory) and channel

✉ S6: (0) 10/698514

જી S7: (0) 10726508

SB: (869076) (column pillar)

S9: (2280019) cylind\$6

☛ S10: 30075091 (Kolumbiyalı) cvlindSR

9780130352373



Bruxes



Cliff

DBS

US:PGPub,USPAT,EPO,JPO,DERWENT,IBM,TDI

P Plurals

Default operator: **OR**

☛ Highlight all the terms in italics.

2 same 5

Jan, 2005

A BRS Form

A IS&B form

Text  IBM

1

	U	I	Inventor	Document#	Issue	P	Title	Current	Current XP	Retrieval	S	C	P	T	Y	Image	Doc	P
1	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	Wu, Ching-Yu	US 2004004	20040	3	VERTICAL DRAM CELL STRUCTURE AND IT	257/301			<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>		US 200400	
2	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	Wu, Ching-Yu	US 2004003	20040	3	SELF-ALIGNED VERTICAL TRANSISTOR DRA	327/296			<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>		US 200400	
3	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	Wu, Ching-Yu	US 2004003	20040	3	VERTICAL TRANSISTOR DRAM STRUCTUR	257/301/257/E29.34			<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>		US 200400	
4	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	Hsieh, Chia-T	US 2001001	20010	8	Method of fabricating buried source to shrin	257/333/257/331			<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>		US 200100	
5	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	Wu, Ching-Yu	US 6734485	20040	3	Vertical DRAM cell structure and its contact	257/301/257/302			<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>		US 673448	
6	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	Wu, Ching-Yu	US 6734484	20040	3	Vertical transistor DRAM structure and its m	257/301/257/302, 2			<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>		US 673448	
7	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	Wu, Ching-Yu	US 6700150	20040	3	Self-aligned vertical transistor DRAM struct	257/296/257/300; 2			<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>		US 670015	
8	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	Wu, Ching-Yu	US 6552382	20030	3	Scalable vertical DRAM cell structure and it	257/305/257/301; 2			<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>		US 655238	
9	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	Hsieh, Chia-T	US 6396112	20020	8	Method of fabricating buried source to shrin	257/394/257/298;			<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>		US 639611	
10	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	Hsieh, Chia-T	US 6207515	20010	9	Method of fabricating buried source to shrin	438/300/257/E21.43			<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>		US 620751	

[x](#) [FRS](#) [Details](#) [HTML](#)

Ready

2004